

20V N-Channel Enhancement Mode MOSFET

Description

The AP3416MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 20V$ $I_D = 6.5A$

$R_{DS(ON)} < 33m\Omega$ @ $V_{GS} = 4.5V$

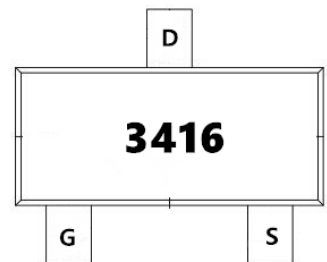
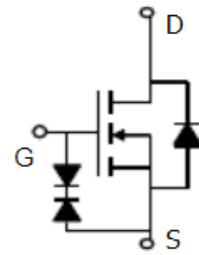
ESD=2500HBM

Application

Battery protection

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP3416MI	SOT-23-3L	3416	3000

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	6.5	A
Drain Current-Pulsed (Note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89	$^\circ C/W$

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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=6.5A$	-	17	27	m Ω
		$V_{GS}=2.5V, I_D=5.5A$	-	21	33	m Ω
		$V_{GS}=1.8V, I_D=5A$	-	28	40	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=6.5A$	8	-	-	S
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	660	-	PF
Output Capacitance	C_{oss}		-	160	-	PF
Reverse Transfer Capacitance	C_{rss}		-	87	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1.5\Omega$ $V_{GS}=5V, R_{GEN}=3\Omega$	-	0.5		nS
Turn-on Rise Time	t_r		-	1		nS
Turn-Off Delay Time	$t_{d(off)}$		-	12		nS
Turn-Off Fall Time	t_f		-	4		nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=6.5A,$ $V_{GS}=4.5V$	-	8		nC
Gate-Source Charge	Q_{gs}		-	2.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=6.5A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	6.5	A

Notes:

Repetitive Rating: Pulse width limited by maximum junction temperature.

Surface Mounted on FR4 Board, $t \leq 10$ sec.

Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Guaranteed by design, not subject to production

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Typical Characteristics

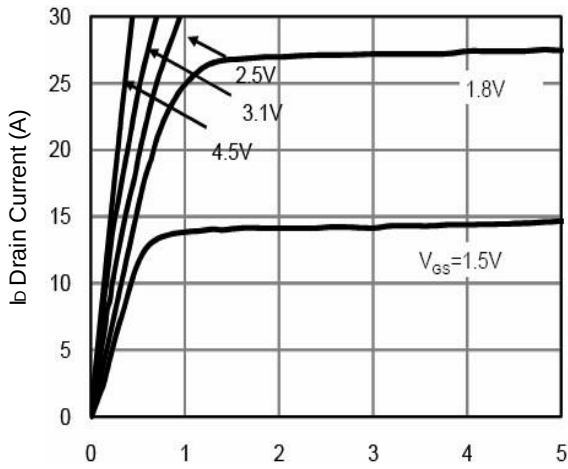


Fig.1 Typical Output Characteristics

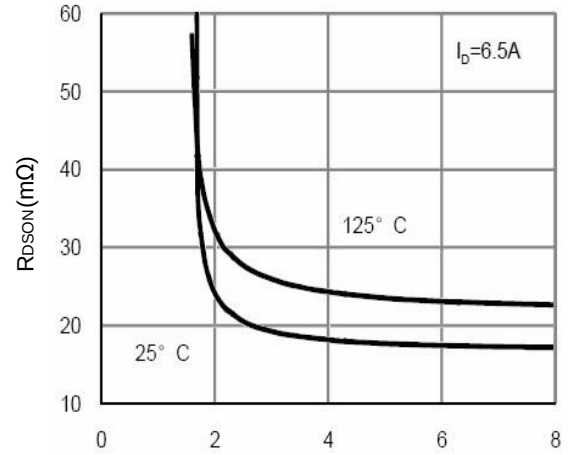


Fig.2 On-Resistance vs. Gate-Source

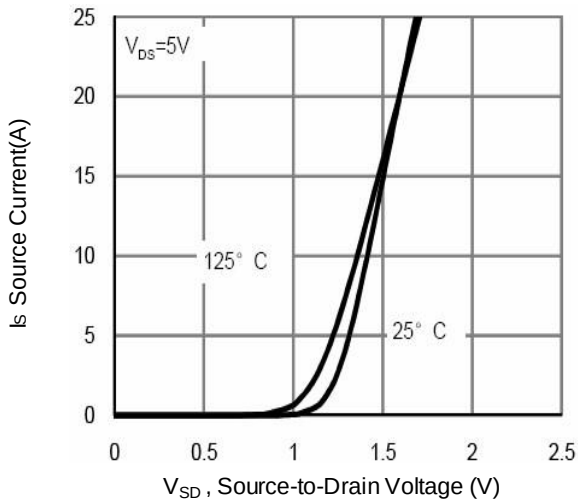


Fig.3 Forward Characteristics of Reverse

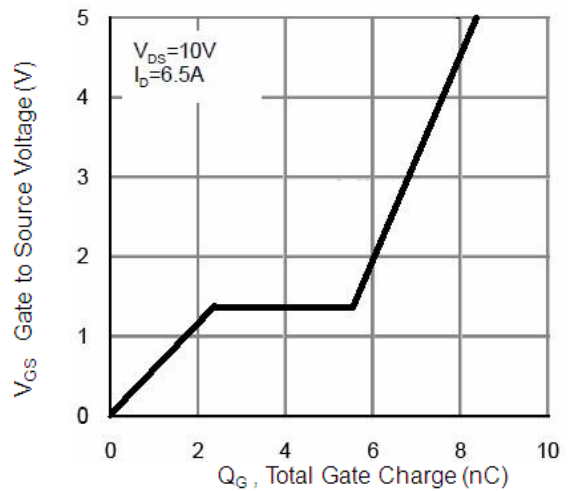


Fig.4 Gate-Charge Characteristics

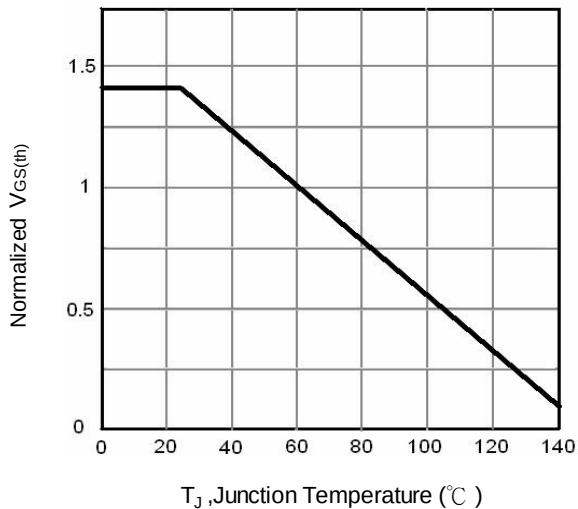


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

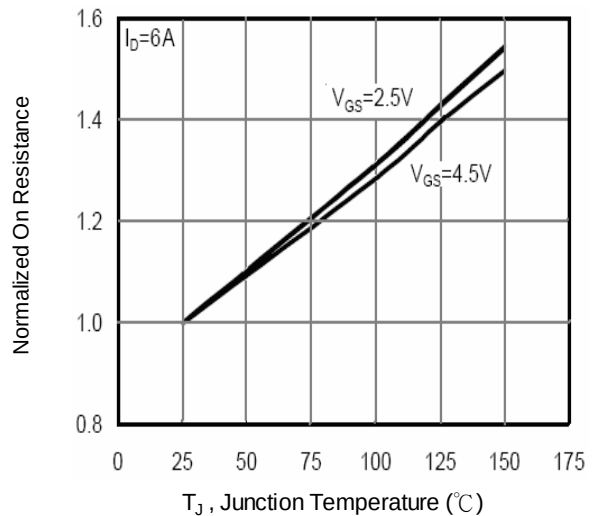


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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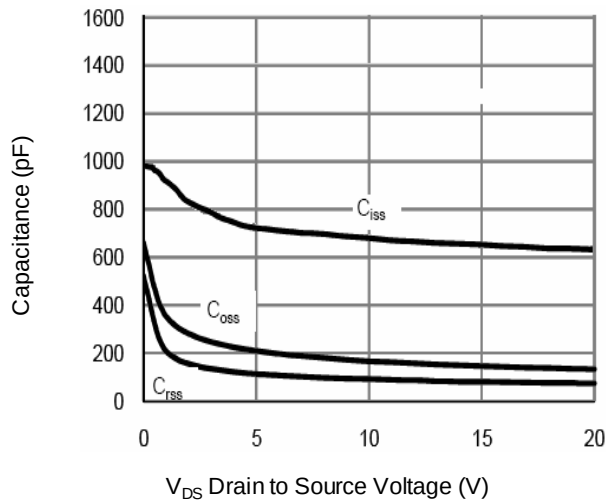


Fig.7 Capacitance

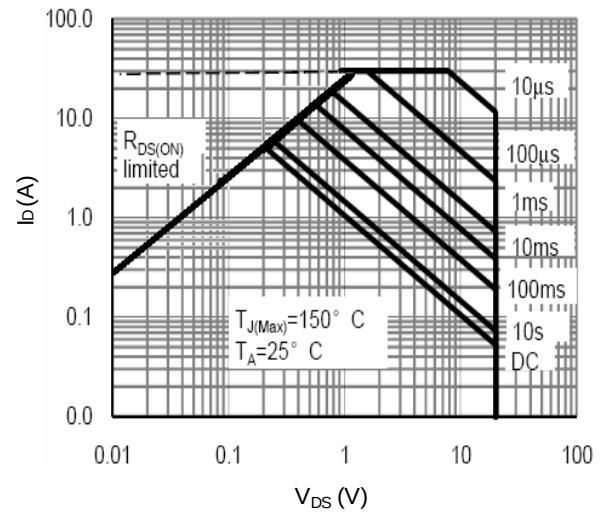


Fig.8 Safe Operating Area

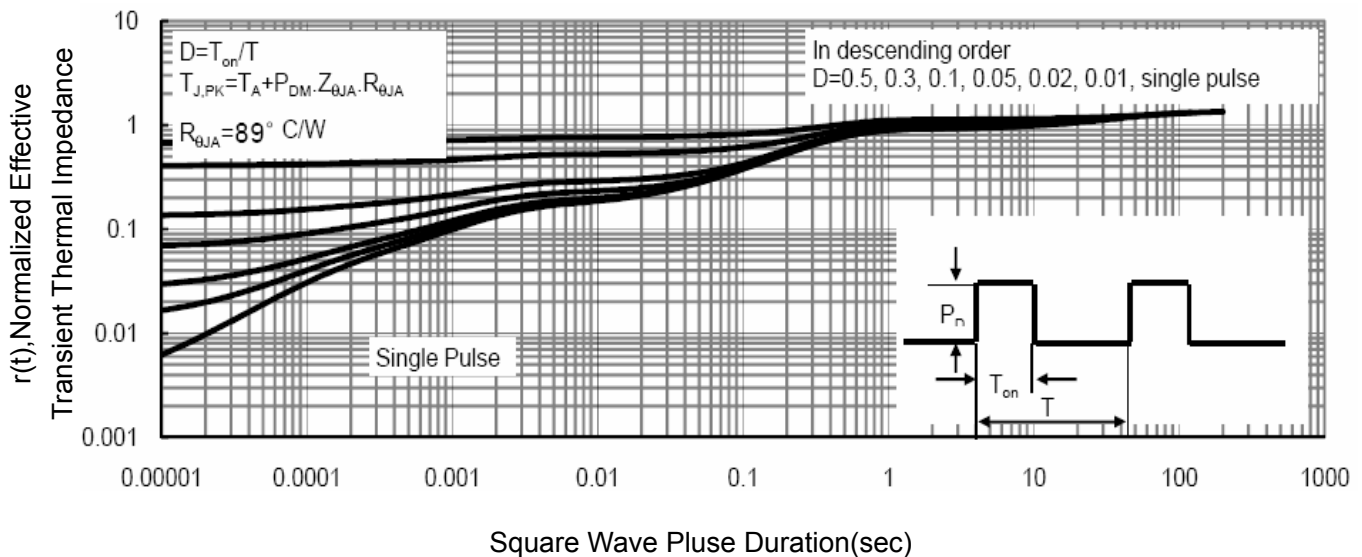


Fig.9 Normalized Maximum Transient Thermal Impedance

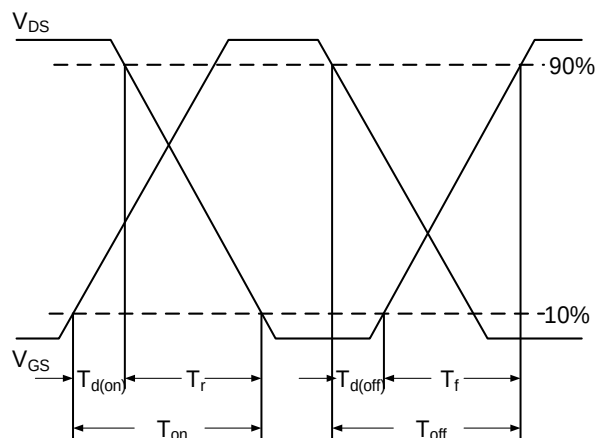


Fig.10 Switching Time Waveform

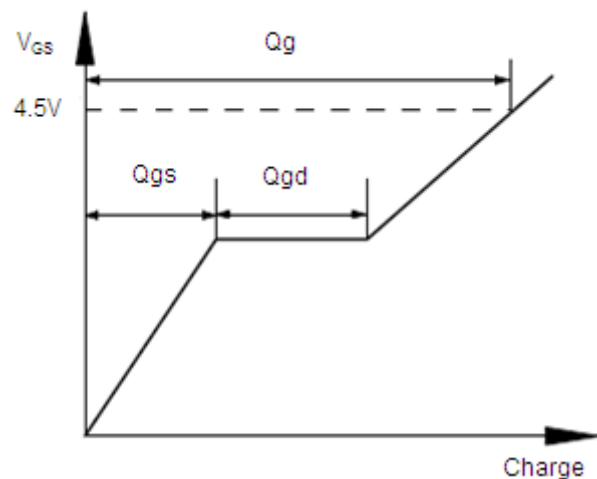
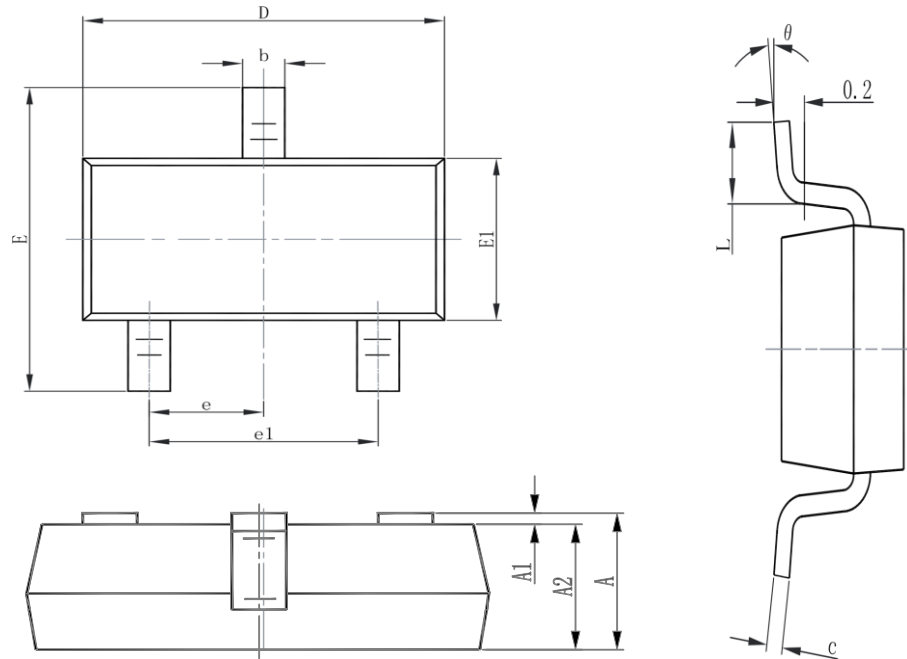


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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